

# MOS FIELD EFFECT TRANSISTOR 2SJ599

# SWITCHING P-CHANNEL POWER MOS FET

### **DESCRIPTION**

The 2SJ599 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

### **FEATURES**

· Low on-state resistance:

 $R_{DS(on)1}$  = 75 m $\Omega$  MAX. (VGS = -10 V, ID = -10 A)

 $R_{DS(on)2}$  = 111 m $\Omega$  MAX. (Vgs = -4.0 V, ID = -10 A)

· Low input capacitance:

 $C_{iss} = 1300 \text{ pF TYP.} (V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V})$ 

- · Built-in gate protection diode
- TO-251/TO-252 package

### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-60	V
Gate to Source Voltage (Vps = 0 V)	Vgss	∓20	V
Drain Current (DC) (Tc = 25°C)	I <sub>D(DC)</sub>	∓20	Α
Drain Current (pulse) Note1	I <sub>D(pulse)</sub>	∓50	Α
Total Power Dissipation (Tc = 25°C)	PT	35	W
Total Power Dissipation (T <sub>A</sub> = 25°C)	PT	1.0	W
Channel Temperature	$T_ch$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C
Single Avalanche Current Note2	las	-20	Α
Single Avalanche Energy Note2	Eas	40	mJ

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

2. Starting T<sub>ch</sub> = 25°C, V<sub>DD</sub> = -30 V, R<sub>G</sub> = 25  $\Omega$ , V<sub>GS</sub> = -20  $\rightarrow$  0 V

### ★ ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ599	TO-251 (MP-3)
2SJ599-Z	TO-252 (MP-3Z)

(TO-251)



(TO-252)



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### **ELECTRICAL CHARACTERISTICS (TA = 25°C)**

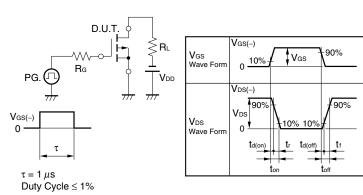
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V			-10	μΑ
Gate Leakage Current	Igss	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$			∓10	μΑ
Gate Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-1.5	-2.0	-2.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -10 A	8	16		S
Drain to Source On-state Resistance	RDS(on)1	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -10 A		60	75	mΩ
	RDS(on)2	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -10 A		78	111	$m\Omega$
Input Capacitance	Ciss	V <sub>DS</sub> = -10 V		1300		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V		240		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		100		pF
Turn-on Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> = -10 A		8		ns
Rise Time	tr	V <sub>GS</sub> = -10 V		9		ns
Turn-off Delay Time	<b>t</b> d(off)	V <sub>DD</sub> = -30 V		52		ns
Fall Time	<b>t</b> f	R <sub>G</sub> = 0 Ω		16		ns
Total Gate Charge	Q <sub>G</sub>	I <sub>D</sub> = -20 A		26		nC
Gate to Source Charge	Qgs	V <sub>DD</sub> = -48 V		5		nC
Gate to Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> = -10 V		7		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1.0		V
Reverse Recovery Time	trr	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		51		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A /μs		102		nC

### TEST CIRCUIT 1 AVALANCHE CAPABILITY

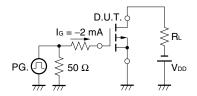
# $V_{GS} = -20 \rightarrow 0 \text{ V}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$

- Starting Tch

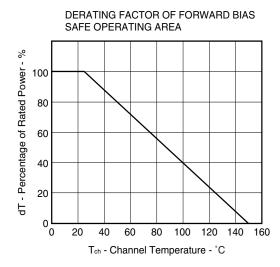
### TEST CIRCUIT 2 SWITCHING TIME

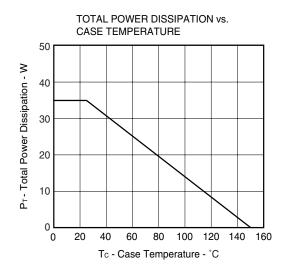


### **TEST CIRCUIT 3 GATE CHARGE**

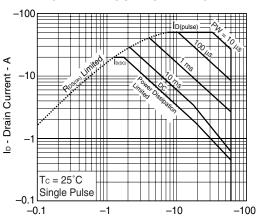


### TYPICAL CHARACTERISTICS (TA = 25°C)



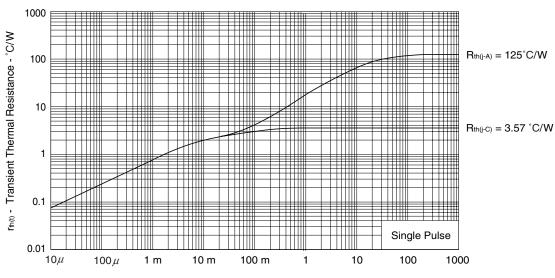


### FORWARD BIAS SAFE OPERATING AREA



 $V_{\text{\scriptsize DS}}$  - Drain to Source Voltage - V

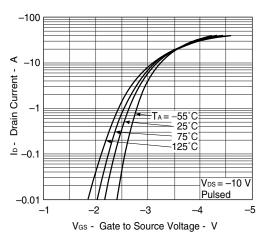
### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



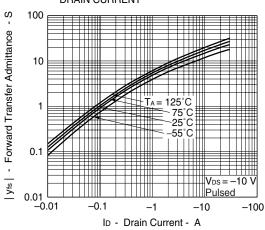
PW - Pulse Width - s

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### FORWARD TRANSFER CHARACTERISTICS



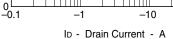
# FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



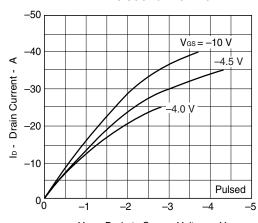
# R<sub>DS(on)</sub> - Drain to Source On-state Resistance - mΩ RESISTANCE vs. DRAIN CURRENT 200 Pulsed 160 120 4.0 V 4.5 V

DRAIN TO SOURCE ON-STATE

–10 V

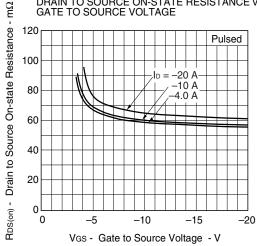


# DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

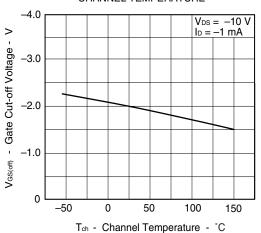


V<sub>DS</sub> - Drain to Source Voltage - V

# DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



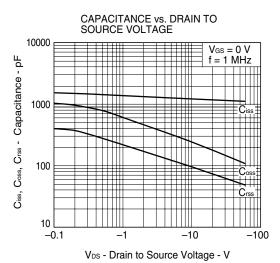
4

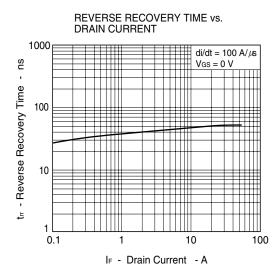
80

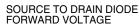
40

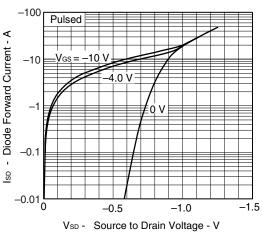
-100

### DRAIN TO SOURCE ON-STATE RESISTANCE vs. ш CHANNEL TEMPERATURE RDS(on) - Drain to Source On-state Resistance -Pulsed -4.0 V Vgs= 100 10 V 50 $I_D = -10 A$ 0 100 150 -50 50 Tch - Channel Temperature - °C

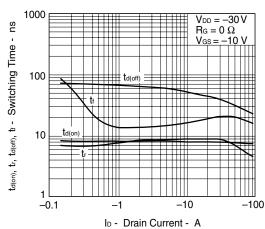




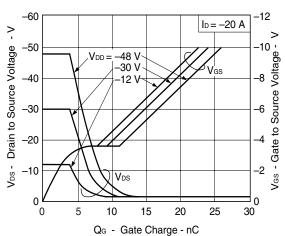


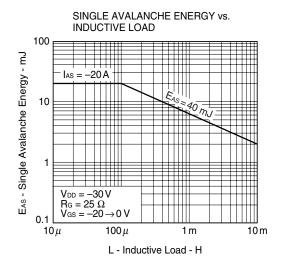


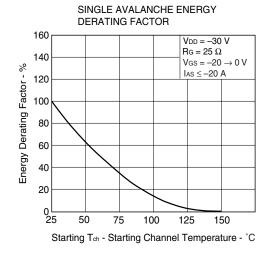
### SWITCHING CHARACTERISTICS



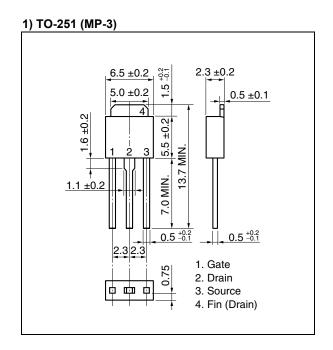
### DYNAMIC INPUT/OUTPUT CHARACTERISTICS

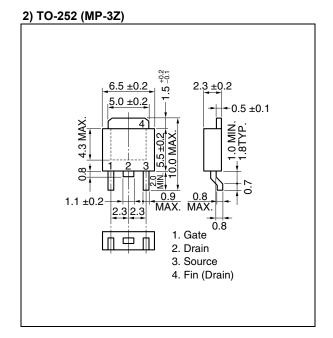




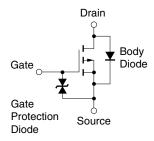


### **★ PACKAGE DRAWINGS (Unit: mm)**





### **EQUIVALENT CIRCUIT**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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